

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	"10612414"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:30
L2	86	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (gate adj (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:32
L3	96	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (gate adj (insulation or insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:32
L4	62	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (gate adj (insulation or insulating or dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:33
L5	13	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (gate adj (insulation or insulating or dielectric)) with (semiconductor adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:34
L6	23	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (gate adj (insulation or insulating or dielectric)) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:36
L7	20	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (gate adj (insulation or insulating or dielectric)) with (semiconductor adj layer) with (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:37
L8	1	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (first adj gate adj (insulation or insulating or dielectric)) with (semiconductor adj layer) with (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:37

L9	1	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (first adj gate adj (insulation or insulating or dielectric)) with (semiconductor adj layer) with (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:37
L10	1	(first adj thin adj film adj transistor) with (second adj thin adj film adj transistor) with (first adj gate adj (insulation or insulating or dielectric)) with (semiconductor adj layer) same (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:37
L11	11	(first adj thin adj film adj transistor) same (second adj thin adj film adj transistor) same (first adj gate adj (insulation or insulating or dielectric)) same (semiconductor adj layer) same (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:41
L12	0	("2004/0048422").URPN.	USPAT	OR	ON	2005/10/30 15:40
L13	11	(first adj thin adj film adj transistor) and (second adj thin adj film adj transistor) same (first adj gate adj (insulation or insulating or dielectric)) same (semiconductor adj layer) same (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:41
L14	13	(first adj thin adj film adj transistor) and (second adj thin adj film adj transistor) same (first adj gate adj (insulation or insulating or dielectric)) and (semiconductor adj layer) same (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:41
L15	20	(first adj thin adj film adj transistor) and (second adj thin adj film adj transistor) and (first adj gate adj (insulation or insulating or dielectric)) and (semiconductor adj layer) same (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:41
L16	32	(first adj thin adj film adj transistor) and (second adj thin adj film adj transistor) and (first adj gate adj (insulation or insulating or dielectric)) and (semiconductor adj layer) and (first adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:42

L17	32	(first adj thin adj film adj transistor) and (second adj thin adj film adj transistor) and (first adj gate adj (insulation or insulating or dielectric)) and (semiconductor adj layer) and (first adj gate adj electrode) and (second adj gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/30 15:42
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